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IN THE CLAIMS

1 (Previously Presented). A method comprising:

forming a phase change memory element having a holding voltage that is at least 80 percent of the threshold voltage of the element and a holding voltage greater than about .9 volts.

Claim 2 (Canceled).

3 (Original). The method of claim 1 including forming a phase change memory element to have a threshold voltage that does not vary by more than 10 percent with programming currents varying as much as two times.

4 (Original). The method of claim 1 including forming a phase change memory element including a phase change material between a pair of electrodes.

5 (Original). The method of claim 4 including forming a phase change material with a lower electrode of titanium silicon nitride.

6 (Previously Presented). An apparatus comprising:

a phase change memory element to be read with a voltage greater than or equal to the threshold voltage of the element, said element having a holding voltage that is at least 80 percent of the threshold voltage of the element.

7 (Original). The apparatus of claim 6 wherein said element includes an upper and a lower electrode and a phase change material between said electrodes.

Claim 8 (Canceled).

9 (Original). The apparatus of claim 6 wherein the phase change memory element has a threshold voltage that varies by less than 10 percent with varying programming currents.

10 (Original). The apparatus of claim 7 wherein said lower electrode includes titanium silicon nitride or carbon.

11 (Previously Presented). A system comprising:

a processor; and

a phase change memory element having a holding voltage that is at least 80 percent of the threshold voltage of the element and said holding voltage being at least about .9 volts.

12 (Previously Presented). The system of claim 11 wherein said wireless interface includes a dipole antenna.

13 (Original). The system of claim 11 wherein said element includes an upper and lower electrode and a phase change material between said electrodes.

14 (Original). The system of claim 13 wherein said lower electrode includes titanium silicon nitride.

Claim 15 (Canceled).

16 (Original). The system of claim 11 wherein the phase change memory element has a threshold voltage that does not vary by more than 10 percent with programming currents varying by as much as two times.

Claims 17-19 (Canceled).